

**UTC** UNISONIC TECHNOLOGIES CO., LTD

# **BTA04** SENSITIVE GATE TRIAC

### DESCRIPTION

The UTC BTA04 is a 4A triac, it uses UTC's advanced technology to provide customers with high commutation performances and voltage insulated tab, etc.

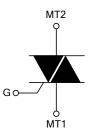
The UTC BTA04 is suitable for inductive loads, general purpose AC switching and an ON/OFF function in applications such as induction motor starting circuits, for phase control operation in light dimmers and static relays, etc.

### **FEATURES**

\* Low gate trigger current

\* Low holding current

### **SYMBOL**



## **ORDERING INFORMATION**

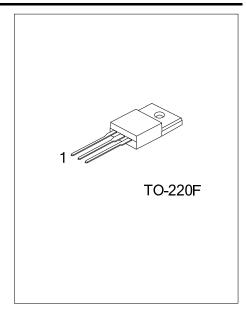
Ordering	Dookogo	Pin /	Assignr	Deaking		
Lead Free	Halogen Free	Package	1	2	3	Packing
BTA04L-x-x-TF3-T	BTA04G-x-x-TF3-T	TO-220F	MT1	MT2	G	Tube

(4)Voltage	<ul> <li>(1) T: Tube</li> <li>(2) TF3: TO-220F</li> <li>(3) refer to SENSITIVITY AND TYPE</li> <li>(4) 4: 400V, 6: 600V, 7: 700V, 8: 800V</li> </ul>
	(5) L: Lead Free, G: Halogen Free and Lead Free

#### SENSITIVITY AND TYPE

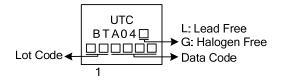
PART NUMBER		VOLT	ΓAGE	SENSITIVITY	TYPE		
PART NUMBER	400V	600V	700V	800V	SENSITIVITY	TTPE	
А	0				10mA	STANDARD	
S			$\bigcirc$	0	10mA	STANDARD	
D		0			5mA	STANDARD	
Т	0	0	$\bigcirc$	$\bigcirc$	5mA	STANDARD	

O: Available



# BTA04

# MARKING





## ■ ABSOLUTE MAXIMUM RATINGS

PARAMETER		SYMBOL	RATINGS	UNIT
RMS On-State Current (360° Conduction Angle)	T <sub>C</sub> =90°C	I <sub>T(RMS)</sub>	4	А
Non Repetitive Surge Peak On-State	t <sub>p</sub> =8.3ms	I <sub>TSM</sub>	42	А
Current (T <sub>J</sub> initial=25°C)	t <sub>p</sub> =10ms	130	40	А
l <sup>2</sup> t Value	t <sub>p</sub> =10ms	l <sup>2</sup> t	8	A <sup>2</sup> s
Critical Rate of Rise of On-State Current:	Repetitive F=50Hz	dl/dt	10	A/µs
I <sub>G</sub> =50mA, dI <sub>G</sub> /dt=0.1A/µs	Non Repetitive	ui/ut	50	A/µs
	400 T/A		400	V
Repetitive Peak Off-State Voltage	600 T/D		600	V
(T <sub>J</sub> =110°C)	700 T/S	V <sub>DRM</sub> /V <sub>RRM</sub>	700	V
	800 T/S		800	V
Peak Gate Current	t <sub>p</sub> =20µs	I <sub>GM</sub>	4	А
Peak Positive Gate Voltage	t <sub>p</sub> =20µs	V <sub>GM</sub>	16	V
Peak Positive Gate Power Dissipation	t <sub>p</sub> =20µs	P <sub>GM)</sub>	40	W
Average Gate Power Dissipation		P <sub>G(AV)</sub>	1	W
Operating Junction Temperature	TJ	-40~+110	°C	
Storage Junction Temperature		T <sub>STG</sub>	-40~+150	°C

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

## THERMAL RESISTANCES

PARAMETER	SYMBOL	RATINGS	UNIT	
Junction to Ambient	$\theta_{JA}$	60	°C/W	
Junction to Case for 360° Conduction Angle (F=50Hz) (AC)	0	3.3	°C/W	
Junction to Case (DC)	θ <sub>JC</sub>	4.4	°C/W	



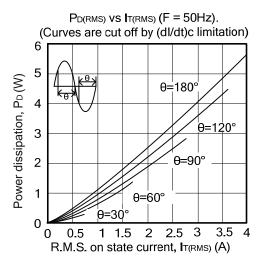
# ELECTRICAL CHARACTERISTICS

		MBOL TEST CONDITIONS		Т		D		S			A					
PARAMETER	SYMBOL	TEST CONDIT	IONS	MIN	TYP	MAX	UNIT									
Gate Trigger	I <sub>GT</sub>	V <sub>D</sub> =12V (DC)	1-11-111			5			5			10			10	mA
Current	IGI	$R_{L}=33\Omega$	IV			5			10			10			25	mA
Gate Trigger Voltage	V <sub>GT</sub>	T <sub>J</sub> =25°C	ALL			1.5			1.5			1.5			1.5	V
Gate Non-Trigger Voltage	$V_{GD}$	V <sub>D</sub> =V <sub>DRM</sub> , R <sub>L</sub> =3.3kΩ, T <sub>J</sub> =110°C	ALL	0.2			0.2			0.2			0.2			V
Time Gate Trigger	t <sub>GT</sub>	V <sub>D</sub> =V <sub>DRM</sub> , I <sub>G</sub> =40mA, dI <sub>G</sub> /dt=0.5A/µs, T <sub>J</sub> =25°C	ALL		2			2			2			2		μs
Holding Current (Note 1)	Ι <sub>Η</sub>	I <sub>T</sub> =100mA, Gate T <sub>J</sub> =25°C	Open,			15			15			25			25	mA
Latching Current	١L	I <sub>G</sub> =1.2I <sub>GT</sub> , T <sub>J</sub> =25°C	-   -  V 		10 20			10 20			20 40			20 40		mA mA
Peak On-State Voltage (Note 1)	V <sub>TM</sub>	I <sub>™</sub> =5.5A, t <sub>p</sub> =380 T <sub>J</sub> =25°C	µs,			1.65			1.65			1.65			1.65	v
Repetitive	I <sub>DRM</sub>	V <sub>DRM</sub> Rated, T <sub>J</sub> =2	25°C			0.01			0.01			0.01			0.01	mA
Peak Off-State Current	I <sub>RRM</sub>	V <sub>RRM</sub> Rated, T <sub>J</sub> =′	110°C			0.75			0.75			0.75			0.75	mA
Critical Rate of Rise of Off-State Voltage (Note 1)	dV/dt	Linear Slope up to V <sub>D</sub> =67%V <sub>DRM</sub> , Gate Open, T <sub>J</sub> =110°C			10			10		10			10			V/µs
Critical Rate of Rise of Off-State Voltage at Commutation (Note 1)	(dV/dt)c	(dl/dt)c=1.8A/ms Tյ=110°C	,		1			1			5			5		V/µs

Note: For either polarity of electrode MT2 voltage with reference to electrode MT1.



## TYPICAL CHARACTERISTICS



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